

# SN74HCS00 シュミット・トリガ入力採用クワッド 2 入力 NAND ゲート

## 1 特長

- 広い動作電圧範囲: 2V~6V
- シュミット・トリガ入力により低速の信号またはノイズの多い信号に対応
- 低い消費電力
  - $I_{CC}$ : 100nA (標準値)
  - 入力リーク電流:  $\pm 100$ nA (標準値)
- 5V で  $\pm 7.8$ mA の出力駆動能力
- 拡張周囲温度範囲:  $-40^{\circ}\text{C} \sim +125^{\circ}\text{C}$ ,  $T_A$

## 2 アプリケーション

- アラーム / タンパ検出回路
- S-R ラッチ

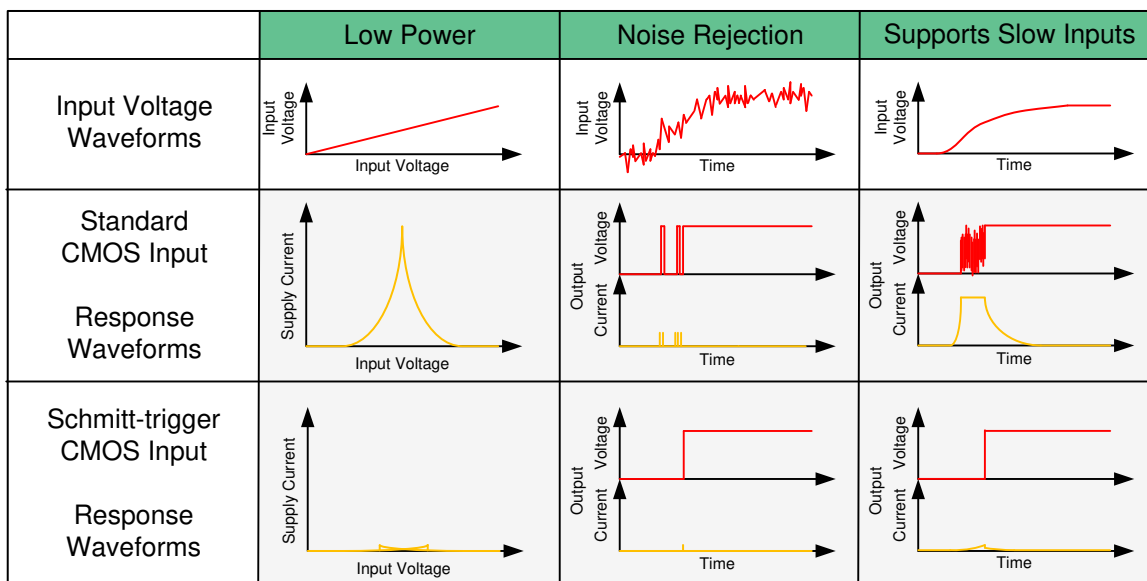
## 3 概要

このデバイスには、シュミット・トリガ入力採用の 4 つの独立した 2 入力 NAND ゲートが内蔵されています。各ゲートはブール関数  $Y = A \bullet B$  を正論理で実行します。

### 製品情報

| 部品番号         | パッケージ <sup>(1)</sup> | 本体サイズ (公称)      |
|--------------|----------------------|-----------------|
| SN74HCS00PW  | TSSOP (14)           | 5.00mm × 4.40mm |
| SN74HCS00D   | SOIC (14)            | 8.70mm × 3.90mm |
| SN74HCS00BQA | WQFN (14)            | 3.00mm × 2.50mm |
| SN74HCS00DYY | SOT-23 (14)          | 4.20mm × 2.00mm |

- (1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



シュミットトリガ入力の利点



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## 4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

### Changes from Revision B (January 2021) to Revision C (December 2021) Page

|                                                                                            |          |
|--------------------------------------------------------------------------------------------|----------|
| • 「製品情報」表に DYY パッケージを追加.....                                                               | <b>1</b> |
| • Added DYY package information to the <i>Pin Configuration and Functions</i> section..... | <b>3</b> |
| • Added DYY package to Thermal Information table.....                                      | <b>5</b> |

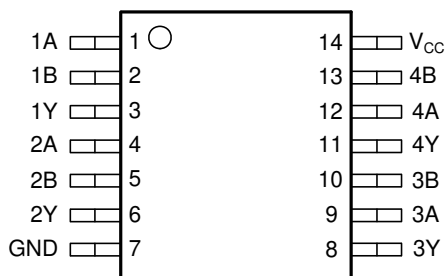
### Changes from Revision A (May 2020) to Revision B (January 2021) Page

|                                                                                 |          |
|---------------------------------------------------------------------------------|----------|
| • 文書全体にわたって表、図、相互参照の採番方法を更新.....                                                | <b>1</b> |
| • 「製品情報」に BQA パッケージの情報を追加 .....                                                 | <b>1</b> |
| • Added BQA package information to <i>Pin Configuration and Functions</i> ..... | <b>3</b> |
| • Added BQA package information to <i>Thermal Information</i> table.....        | <b>5</b> |

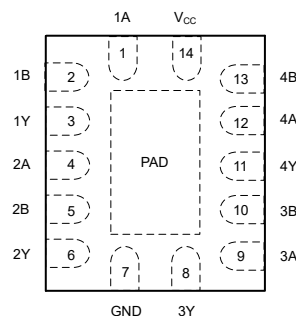
### Changes from Revision \* (December 2019) to Revision A (May 2020) Page

|                                                                               |          |
|-------------------------------------------------------------------------------|----------|
| • 「製品情報」表に D パッケージを追加.....                                                    | <b>1</b> |
| • Added D package information to <i>Pin Configuration and Functions</i> ..... | <b>3</b> |
| • Added D package column to <i>Thermal Information</i> table.....             | <b>5</b> |

## 5 Pin Configuration and Functions



**5-1. D, DYY, or PW Package  
14-Pin SOIC, SOT-23, or TSSOP  
Top View**



**5-2. BQA Package  
14-Pin WQFN  
Top View**

**表 5-1. Pin Functions**

| PIN                        |     | I/O    | DESCRIPTION                                                                                            |
|----------------------------|-----|--------|--------------------------------------------------------------------------------------------------------|
| NAME                       | NO. |        |                                                                                                        |
| 1A                         | 1   | Input  | Channel 1, Input A                                                                                     |
| 1B                         | 2   | Input  | Channel 1, Input B                                                                                     |
| 1Y                         | 3   | Output | Channel 1, Output Y                                                                                    |
| 2A                         | 4   | Input  | Channel 2, Input A                                                                                     |
| 2B                         | 5   | Input  | Channel 2, Input B                                                                                     |
| 2Y                         | 6   | Output | Channel 2, Output Y                                                                                    |
| GND                        | 7   | —      | Ground                                                                                                 |
| 3Y                         | 8   | Output | Channel 3, Output Y                                                                                    |
| 3A                         | 9   | Input  | Channel 3, Input A                                                                                     |
| 3B                         | 10  | Input  | Channel 3, Input B                                                                                     |
| 4Y                         | 11  | Output | Channel 4, Output Y                                                                                    |
| 4A                         | 12  | Input  | Channel 4, Input A                                                                                     |
| 4B                         | 13  | Input  | Channel 4, Input B                                                                                     |
| V <sub>CC</sub>            | 14  | —      | Positive Supply                                                                                        |
| Thermal Pad <sup>(1)</sup> |     | —      | The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply |

(1) BQA Package only.

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

|           |                                            |                                                        | MIN  | MAX | UNIT |
|-----------|--------------------------------------------|--------------------------------------------------------|------|-----|------|
| $V_{CC}$  | Supply voltage                             |                                                        | –0.5 | 7   | V    |
| $I_{IK}$  | Input clamp current <sup>(2)</sup>         | $V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$ |      | ±20 | mA   |
| $I_{OK}$  | Output clamp current <sup>(2)</sup>        | $V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$ |      | ±20 | mA   |
| $I_O$     | Continuous output current                  | $V_O = 0$ to $V_{CC}$                                  |      | ±35 | mA   |
|           | Continuous current through $V_{CC}$ or GND |                                                        |      | ±70 | mA   |
| $T_J$     | Junction temperature <sup>(3)</sup>        |                                                        |      | 150 | °C   |
| $T_{stg}$ | Storage temperature                        |                                                        | –65  | 150 | °C   |

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

(3) Assured by design.

### 6.2 ESD Ratings

|             |                         |                                                                       | VALUE | UNIT |
|-------------|-------------------------|-----------------------------------------------------------------------|-------|------|
| $V_{(ESD)}$ | Electrostatic discharge | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>     | ±4000 | V    |
|             |                         | Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup> | ±1500 |      |

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

|                     |                                     | MIN | NOM | MAX       | UNIT |
|---------------------|-------------------------------------|-----|-----|-----------|------|
| $V_{CC}$            | Supply voltage                      | 2   | 5   | 6         | V    |
| $V_I$               | Input voltage                       | 0   |     | $V_{CC}$  | V    |
| $V_O$               | Output voltage                      | 0   |     | $V_{CC}$  | V    |
| $\Delta t/\Delta v$ | Input transition rise and fall rate |     |     | Unlimited | ns/V |
| $T_A$               | Ambient temperature                 | –55 |     | 125       | °C   |

## 6.4 Thermal Information

| THERMAL METRIC <sup>(1)</sup> |                                              | SN74HCS00  |          |            |           | UNIT |
|-------------------------------|----------------------------------------------|------------|----------|------------|-----------|------|
|                               |                                              | PW (TSSOP) | D (SOIC) | BQA (WQFN) | DYY (SOT) |      |
|                               |                                              | 14 PINS    | 14 PINS  | 14 PINS    | 14 PINS   |      |
| R <sub>θJA</sub>              | Junction-to-ambient thermal resistance       | 151.7      | 133.6    | 109.7      | 236.5     | °C/W |
| R <sub>θJC(top)</sub>         | Junction-to-case (top) thermal resistance    | 79.4       | 89.0     | 111.0      | 143.2     | °C/W |
| R <sub>θJB</sub>              | Junction-to-board thermal resistance         | 94.7       | 89.5     | 77.9       | 146.0     | °C/W |
| Ψ <sub>JT</sub>               | Junction-to-top characterization parameter   | 25.2       | 45.5     | 20.2       | 29.5      | °C/W |
| Ψ <sub>JB</sub>               | Junction-to-board characterization parameter | 94.1       | 89.1     | 77.8       | 145.6     | °C/W |
| R <sub>θJC(bot)</sub>         | Junction-to-case (bottom) thermal resistance | N/A        | N/A      | 56.6       | N/A       | °C/W |

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 6.5 Electrical Characteristics

over operating free-air temperature range; typical ratings measured at T<sub>A</sub> = 25°C (unless otherwise noted).

| PARAMETER       |                                                 | TEST CONDITIONS                                           |                           | V <sub>CC</sub> | MIN                   | TYP                     | MAX   | UNIT |
|-----------------|-------------------------------------------------|-----------------------------------------------------------|---------------------------|-----------------|-----------------------|-------------------------|-------|------|
| V <sub>T+</sub> | Positive switching threshold                    |                                                           |                           | 2 V             | 0.7                   |                         | 1.5   | V    |
|                 |                                                 |                                                           |                           | 4.5 V           | 1.7                   |                         | 3.15  |      |
|                 |                                                 |                                                           |                           | 6 V             | 2.1                   |                         | 4.2   |      |
| V <sub>T-</sub> | Negative switching threshold                    |                                                           |                           | 2 V             | 0.3                   |                         | 1.0   | V    |
|                 |                                                 |                                                           |                           | 4.5 V           | 0.9                   |                         | 2.2   |      |
|                 |                                                 |                                                           |                           | 6 V             | 1.2                   |                         | 3.0   |      |
| ΔV <sub>T</sub> | Hysteresis (V <sub>T+</sub> - V <sub>T-</sub> ) |                                                           |                           | 2 V             | 0.2                   |                         | 1.0   | V    |
|                 |                                                 |                                                           |                           | 4.5 V           | 0.4                   |                         | 1.4   |      |
|                 |                                                 |                                                           |                           | 6 V             | 0.6                   |                         | 1.6   |      |
| V <sub>OH</sub> | High-level output voltage                       | V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>       | I <sub>OH</sub> = -20 μA  | 2 V to 6 V      | V <sub>CC</sub> - 0.1 | V <sub>CC</sub> - 0.002 |       | V    |
|                 |                                                 |                                                           | I <sub>OH</sub> = -6 mA   | 4.5 V           | 4.0                   | 4.3                     |       |      |
|                 |                                                 |                                                           | I <sub>OH</sub> = -7.8 mA | 6 V             | 5.4                   | 5.75                    |       |      |
| V <sub>OL</sub> | Low-level output voltage                        | V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>       | I <sub>OL</sub> = 20 μA   | 2 V to 6 V      |                       | 0.002                   | 0.1   | V    |
|                 |                                                 |                                                           | I <sub>OL</sub> = 6 mA    | 4.5 V           |                       | 0.18                    | 0.30  |      |
|                 |                                                 |                                                           | I <sub>OL</sub> = 7.8 mA  | 6 V             |                       | 0.22                    | 0.33  |      |
| I <sub>I</sub>  | Input leakage current                           | V <sub>I</sub> = V <sub>CC</sub> or 0                     |                           | 6 V             |                       | ±100                    | ±1000 | nA   |
| I <sub>CC</sub> | Supply current                                  | V <sub>I</sub> = V <sub>CC</sub> or 0, I <sub>O</sub> = 0 |                           | 6 V             |                       | 0.1                     | 2     | μA   |
| C <sub>i</sub>  | Input capacitance                               |                                                           |                           | 2 V to 6 V      |                       |                         | 5     | pF   |
| C <sub>pd</sub> | Power dissipation capacitance per gate          | No load                                                   |                           | 2 V to 6 V      |                       | 10                      |       | pF   |

## 6.6 Switching Characteristics

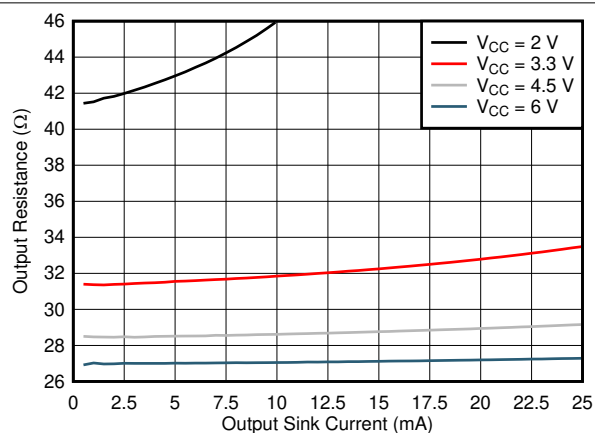
$C_L = 50$  pF; over operating free-air temperature range; typical values measured at  $T_A = 25^\circ\text{C}$  (unless otherwise noted).

See *Parameter Measurement Information*

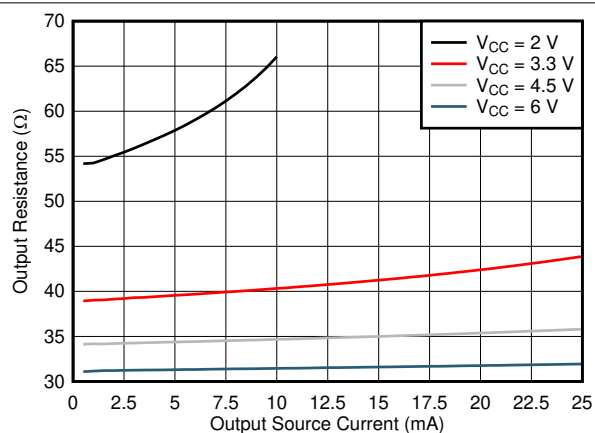
| PARAMETER |                   | FROM (INPUT) | TO (OUTPUT) | $V_{CC}$ | MIN | TYP | MAX | UNIT |
|-----------|-------------------|--------------|-------------|----------|-----|-----|-----|------|
| $t_{pd}$  | Propagation delay | A or B       | Y           | 2 V      |     | 15  | 36  | ns   |
|           |                   |              |             | 4.5 V    |     | 7   | 13  |      |
|           |                   |              |             | 6 V      |     | 5   | 12  |      |
| $t_t$     | Transition-time   |              | Y           | 2 V      |     | 9   | 16  | ns   |
|           |                   |              |             | 4.5 V    |     | 5   | 9   |      |
|           |                   |              |             | 6 V      |     | 4   | 8   |      |

## 6.7 Typical Characteristics

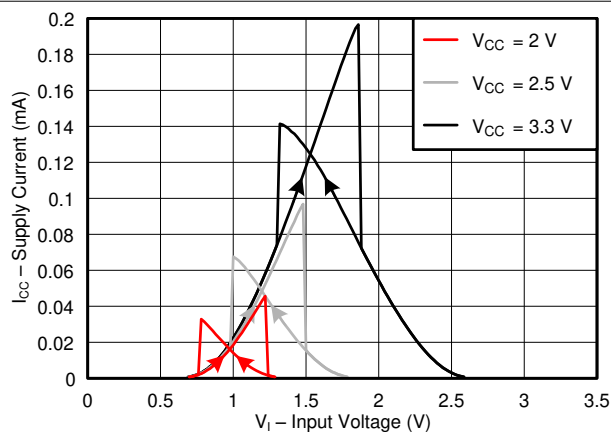
$T_A = 25^\circ\text{C}$



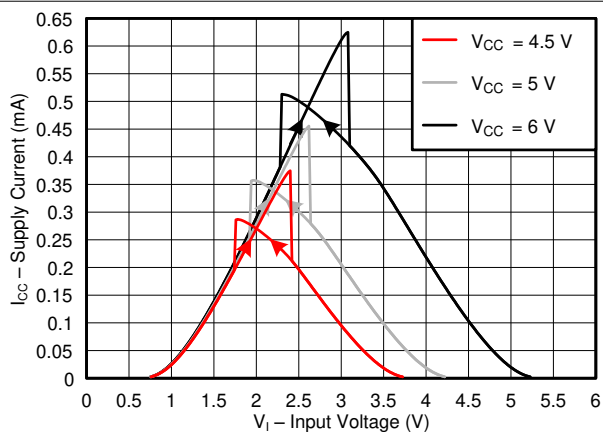
**6-1. Output Driver Resistance in Low State**



**6-2. Output Driver Resistance in High State**



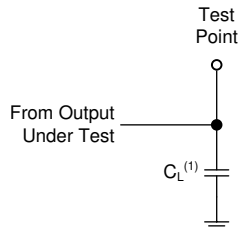
**6-3. Typical Supply Current vs Input Voltage Across Common Supply Values (2 V to 3.3 V)**



**6-4. Typical Supply Current vs Input Voltage Across Common Supply Values (4.5 V to 6 V)**

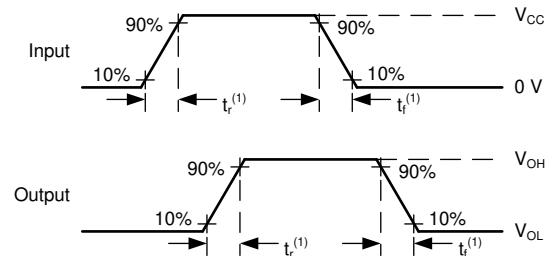
## 7 Parameter Measurement Information

- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 1 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_f < 2.5 \text{ ns}$ .
- The outputs are measured one at a time, with one input transition per measurement.

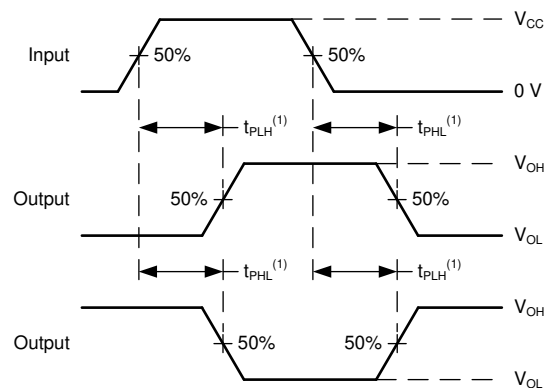


A.  $C_L = 50 \text{ pF}$  and includes probe and jig capacitance.

**FIG 7-1. Load Circuit**



**FIG 7-2. Voltage Waveforms Transition Times**



A. The maximum between  $t_{PLH}$  and  $t_{PHL}$  is used for  $t_{pd}$ .

**FIG 7-3. Voltage Waveforms Propagation Delays**

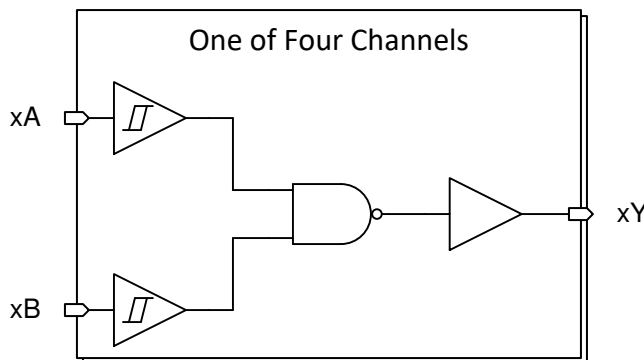


## 8 Detailed Description

### 8.1 Overview

This device contains four independent 2-input NAND Gates with Schmitt-trigger inputs. Each gate performs the Boolean function  $Y = \overline{A \bullet B}$  in positive logic.

### 8.2 Functional Block Diagram



### 8.3 Feature Description

#### 8.3.1 Balanced CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to over-current. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

#### 8.3.2 CMOS Schmitt-Trigger Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using ohm's law ( $R = V \div I$ ).

The Schmitt-trigger input architecture provides hysteresis as defined by  $\Delta V_T$  in the *Electrical Characteristics*, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs slowly will also increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see [Understanding Schmitt Triggers](#).

#### 8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in [Figure 8-1](#).

#### CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

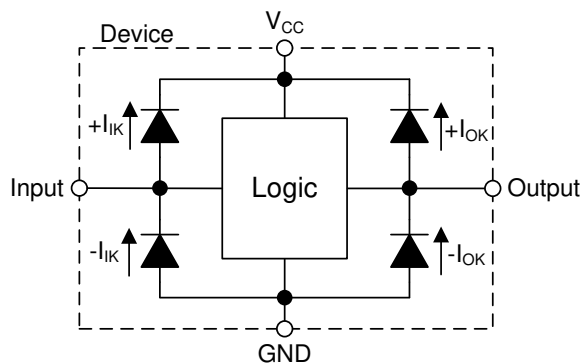


图 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

## 8.4 Device Functional Modes

表 8-1. Function Table

| INPUTS |   | OUTPUT<br>Y |
|--------|---|-------------|
| A      | B |             |
| H      | H | L           |
| L      | X | H           |
| X      | L | H           |

## 9 Application and Implementation

### Note

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

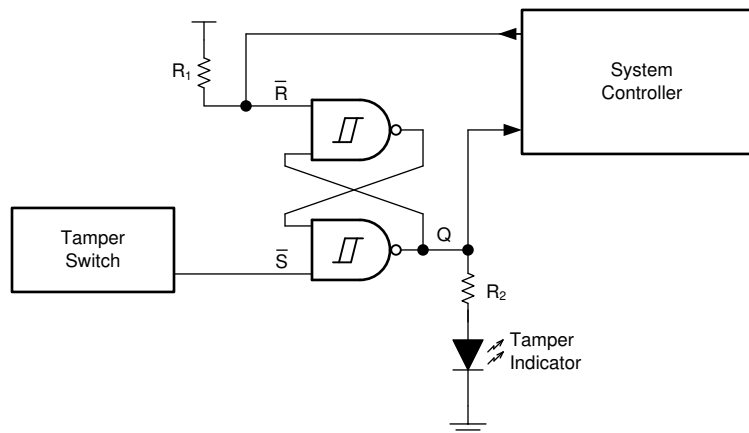
### 9.1 Application Information

In this application, two 2-input NAND gates are used to create an active-low SR latch as shown in [Figure 9-1](#). The two additional gates can be used for a second SR latch, or the inputs can be grounded and both channels left unused.

The SN74HCS00 is used to drive the tamper indicator LED and provide one bit of data to the system controller. When the tamper switch outputs LOW, the output Q becomes HIGH. This output remains HIGH until the system controller addresses the event and sends a LOW signal to the  $\bar{R}$  input which returns the Q output back to LOW.

The inputs of this active-low SR latch can often be driven by open-drain outputs which can produce slow input transition rates when they transition from LOW to Hi-Z. This makes the SN74HCS00 ideal for the application because it has Schmitt-trigger inputs that do not have input transition rate requirements.

### 9.2 Typical Application



**Figure 9-1. Typical Application Block Diagram**

#### 9.2.1 Design Requirements

- All signals in the system operate at 5 V
- Avoid unstable state by not having LOW signals on both inputs
- Q output is HIGH when  $\bar{S}$  is LOW
  - Q output remains High until  $\bar{R}$  is LOW

##### 9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCS00 plus the maximum supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*. The logic device can only source or sink as much current as it is provided at the supply and ground pins, respectively. Be sure not to exceed the maximum total current through GND or  $V_{CC}$  listed in the *Absolute Maximum Ratings*.

The SN74HCS00 can drive a load with a total capacitance less than or equal to 50 pF connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 50 pF.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and  \$C\_{pd}\$  Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

#### CAUTION

The maximum junction temperature,  $T_J(\text{max})$  listed in the *Absolute Maximum Ratings*, is an *additional limitation* to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

#### 9.2.1.2 Input Considerations

Input signals must cross  $V_{t-}(\text{min})$  to be considered a logic LOW, and  $V_{t+}(\text{max})$  to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either  $V_{CC}$  or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCS00, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k $\Omega$  resistor value is often used due to these factors.

The SN74HCS00 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the  $\Delta V_T(\text{min})$  in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than  $V_{CC}$  or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

#### 9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. Similarly, the ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Electrical Characteristics*.

Push-pull outputs that could be in the opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to  $V_{CC}$  or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

### 9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from  $V_{CC}$  to GND. The capacitor needs to be placed physically close to the device and electrically close to both the  $V_{CC}$  and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is  $\leq 50$  pF. This is not a hard limit; however, it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS00 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than  $(V_{CC} / I_{O(max)}) \Omega$ . This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates; however, the power consumption and thermal increase can be calculated using the steps provided in the [CMOS Power Consumption and Cpd Calculation](#) application report.

### 9.2.3 Application Curves

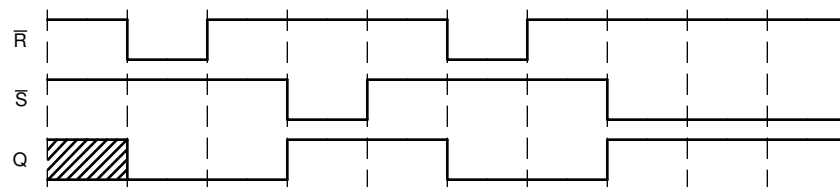


FIG 9-2. Application Timing Diagram

## 10 Power Supply Recommendations

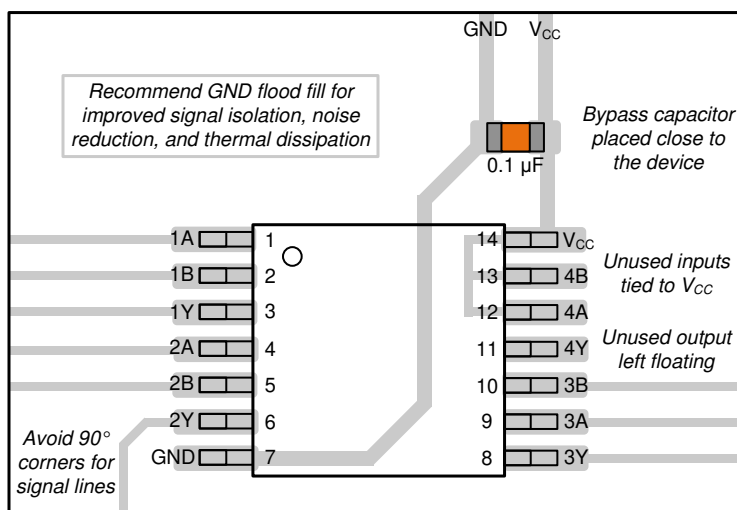
The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu$ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in the following layout example.

## 11 Layout

### 11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or VCC, whichever makes more sense for the logic function or is more convenient.

### 11.2 Layout Example



✎ 11-1. Example Layout for the SN74HCS00

## 12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [HCMOS Design Considerations application report](#)
- Texas Instruments, [CMOS Power Consumption and CPD Calculation application report](#)
- Texas Instruments, [Designing with Logic application report](#)

### 12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](#). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 12.3 サポート・リソース

**TI E2E™ サポート・フォーラム**は、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

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### 12.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

### 12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 12.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

| Orderable part number         | Status<br>(1) | Material type<br>(2) | Package   Pins            | Package qty   Carrier | RoHS<br>(3) | Lead finish/<br>Ball material<br>(4) | MSL rating/<br>Peak reflow<br>(5) | Op temp (°C) | Part marking<br>(6) |
|-------------------------------|---------------|----------------------|---------------------------|-----------------------|-------------|--------------------------------------|-----------------------------------|--------------|---------------------|
| <a href="#">SN74HCS00BQAR</a> | Active        | Production           | WQFN (BQA)   14           | 3000   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HCS00               |
| SN74HCS00BQAR.A               | Active        | Production           | WQFN (BQA)   14           | 3000   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HCS00               |
| <a href="#">SN74HCS00DR</a>   | Active        | Production           | SOIC (D)   14             | 2500   LARGE T&R      | Yes         | NIPDAU   SN                          | Level-1-260C-UNLIM                | -40 to 125   | HCS00               |
| SN74HCS00DR.A                 | Active        | Production           | SOIC (D)   14             | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HCS00               |
| <a href="#">SN74HCS00DYYR</a> | Active        | Production           | SOT-23-THIN<br>(DYY)   14 | 3000   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HCS00               |
| SN74HCS00DYYR.A               | Active        | Production           | SOT-23-THIN<br>(DYY)   14 | 3000   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HCS00               |
| <a href="#">SN74HCS00PWR</a>  | Active        | Production           | TSSOP (PW)   14           | 2000   LARGE T&R      | Yes         | NIPDAU   SN                          | Level-1-260C-UNLIM                | -40 to 125   | HCS00               |
| SN74HCS00PWR.A                | Active        | Production           | TSSOP (PW)   14           | 2000   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 125   | HCS00               |

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

<sup>(4)</sup> **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative



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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

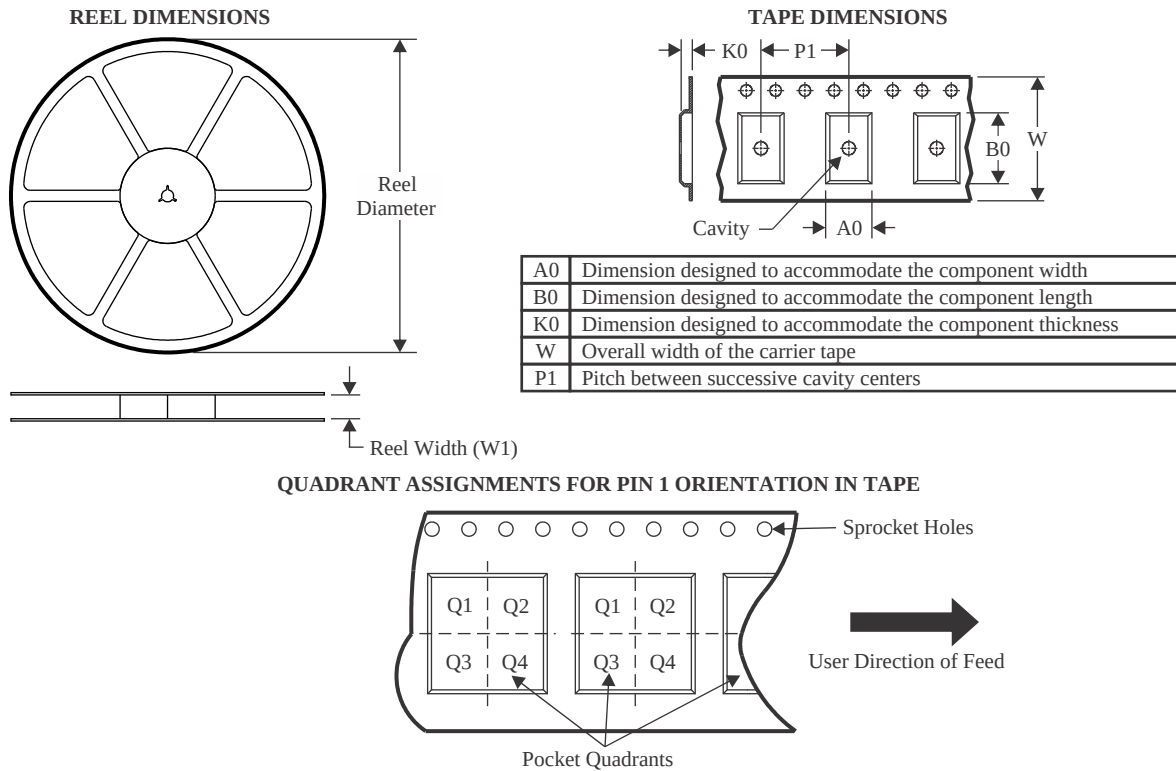
**OTHER QUALIFIED VERSIONS OF SN74HCS00 :**

- Automotive : [SN74HCS00-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

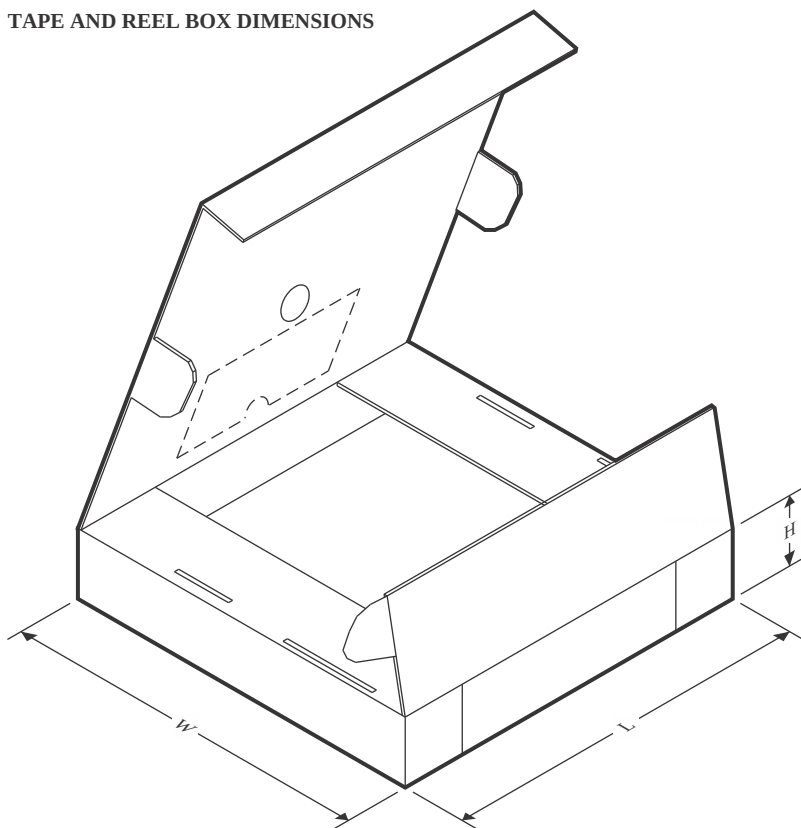
## TAPE AND REEL INFORMATION



\*All dimensions are nominal

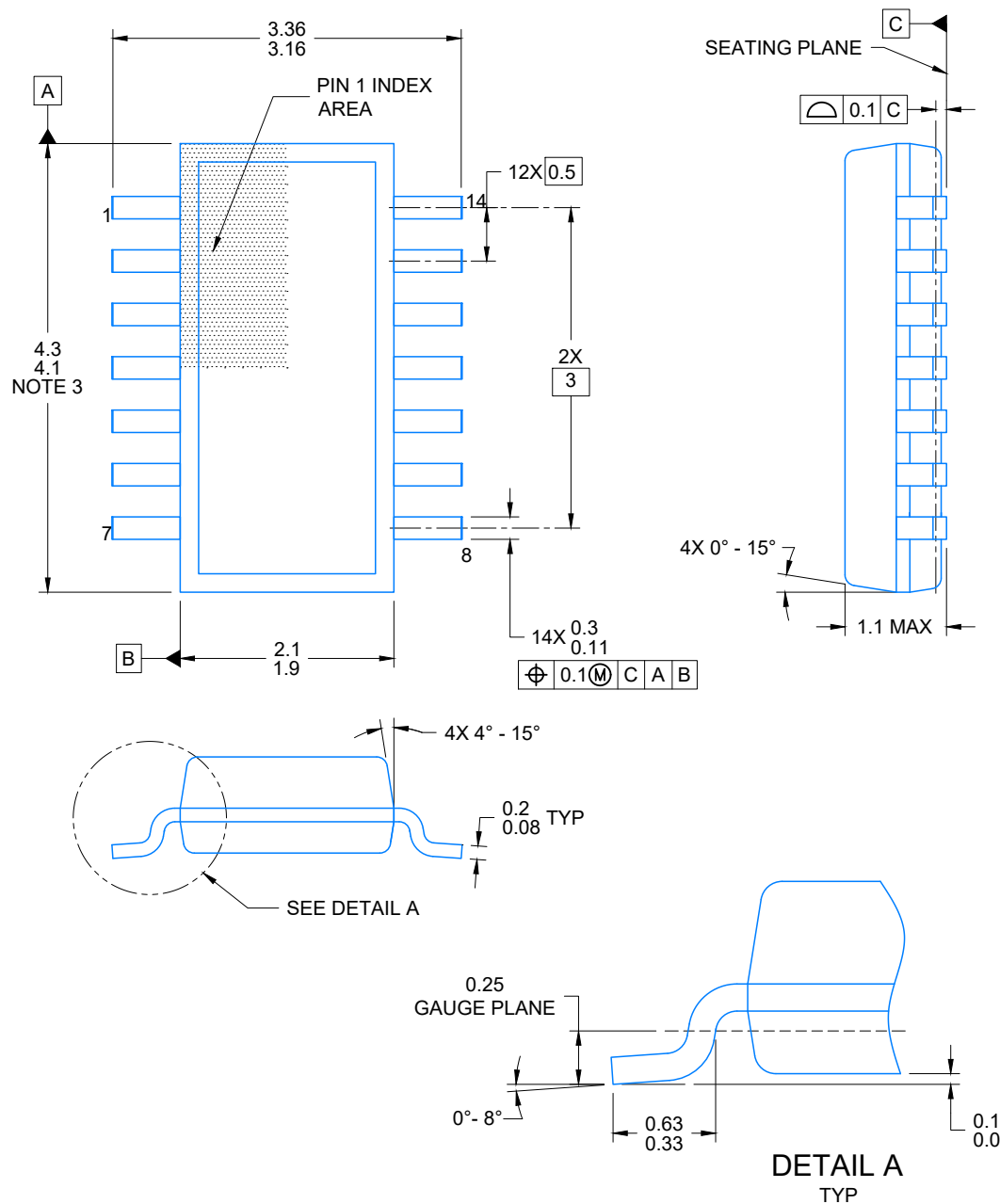
| Device        | Package Type | Package Drawing | Pins | SPQ  | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|---------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| SN74HCS00BQAR | WQFN         | BQA             | 14   | 3000 | 180.0              | 12.4               | 2.8     | 3.3     | 1.1     | 4.0     | 12.0   | Q1            |
| SN74HCS00DR   | SOIC         | D               | 14   | 2500 | 330.0              | 16.4               | 6.6     | 9.3     | 2.1     | 8.0     | 16.0   | Q1            |
| SN74HCS00DR   | SOIC         | D               | 14   | 2500 | 330.0              | 16.4               | 6.5     | 9.0     | 2.1     | 8.0     | 16.0   | Q1            |
| SN74HCS00DYYR | SOT-23-THIN  | DYY             | 14   | 3000 | 330.0              | 12.4               | 4.8     | 3.6     | 1.6     | 8.0     | 12.0   | Q3            |
| SN74HCS00PWR  | TSSOP        | PW              | 14   | 2000 | 330.0              | 12.4               | 6.9     | 5.6     | 1.6     | 8.0     | 12.0   | Q1            |

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

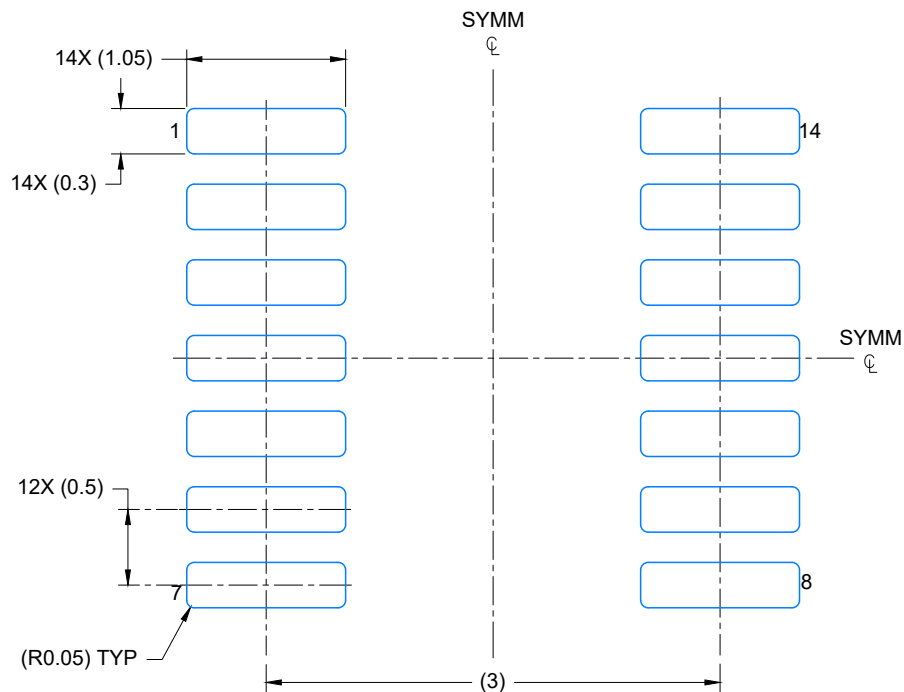
| Device        | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|---------------|--------------|-----------------|------|------|-------------|------------|-------------|
| SN74HCS00BQAR | WQFN         | BQA             | 14   | 3000 | 210.0       | 185.0      | 35.0        |
| SN74HCS00DR   | SOIC         | D               | 14   | 2500 | 366.0       | 364.0      | 50.0        |
| SN74HCS00DR   | SOIC         | D               | 14   | 2500 | 353.0       | 353.0      | 32.0        |
| SN74HCS00DYYR | SOT-23-THIN  | DYY             | 14   | 3000 | 336.6       | 336.6      | 31.8        |
| SN74HCS00PWR  | TSSOP        | PW              | 14   | 2000 | 356.0       | 356.0      | 35.0        |



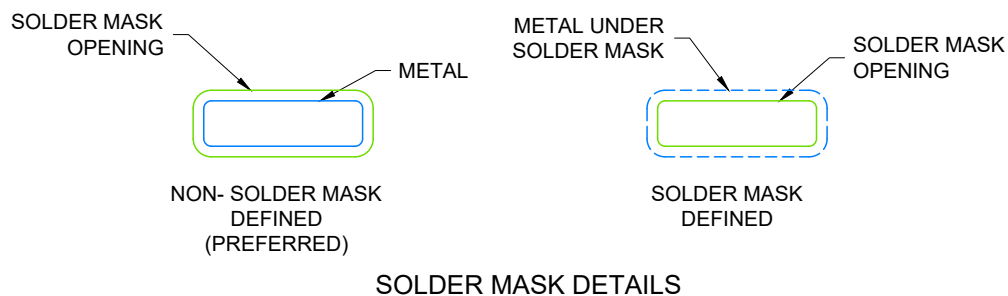
4224643/D 07/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
5. Reference JEDEC Registration MO-345, Variation AB



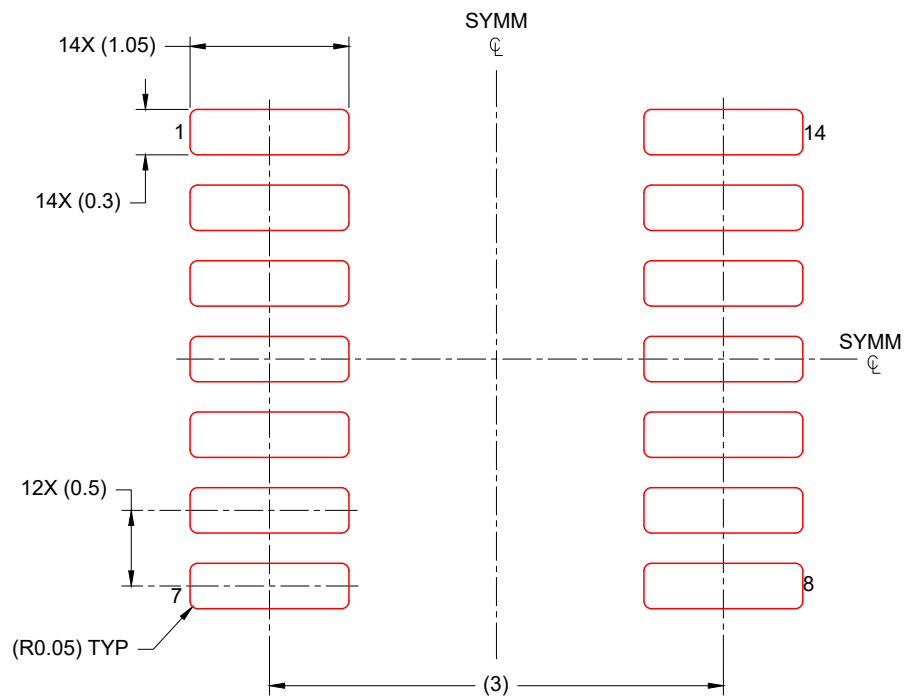
LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 20X



4224643/D 07/2024

## NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

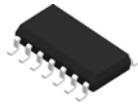


SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE: 20X

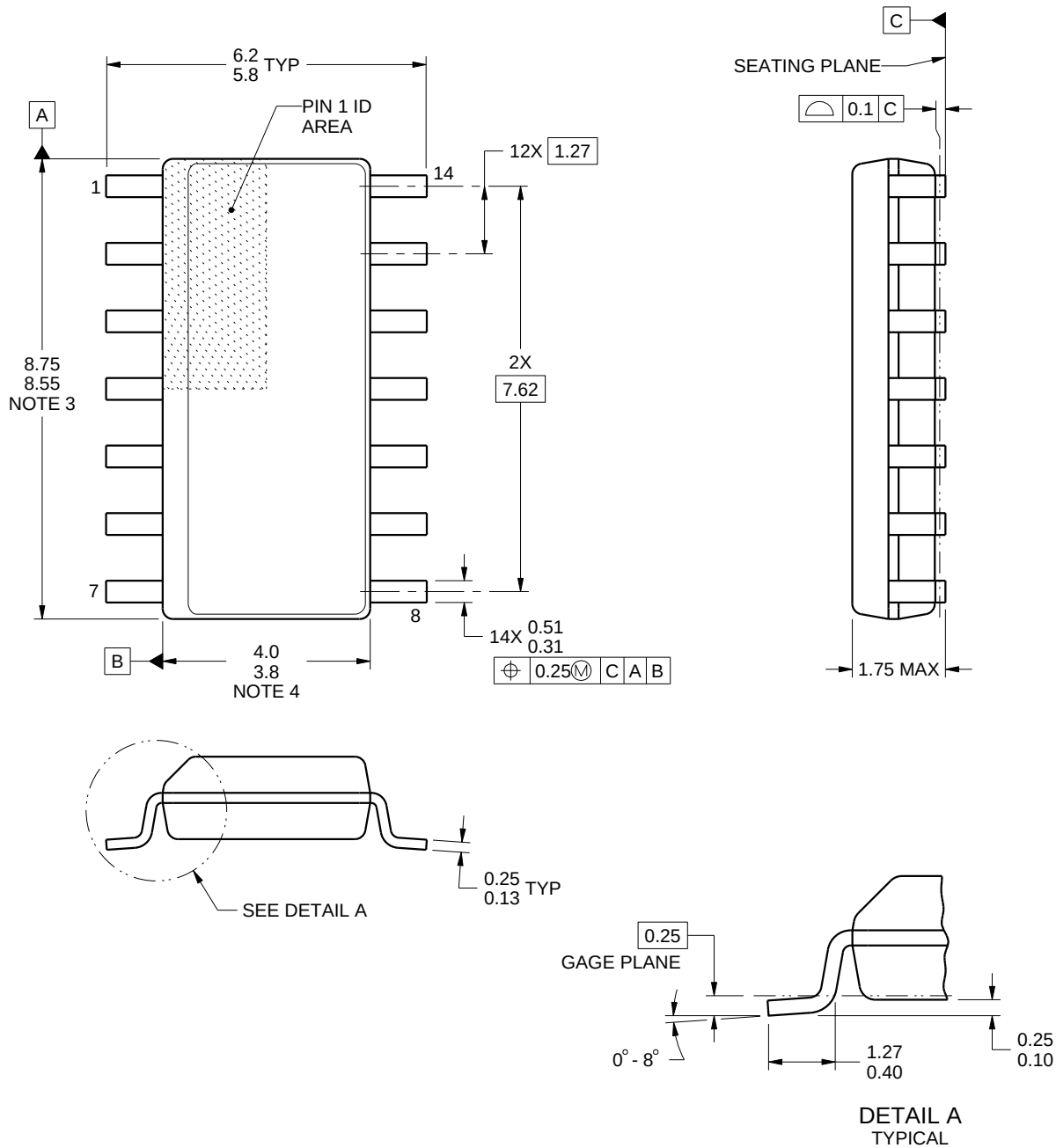
4224643/D 07/2024

## NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

**D0014A****PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4220718/A 09/2016

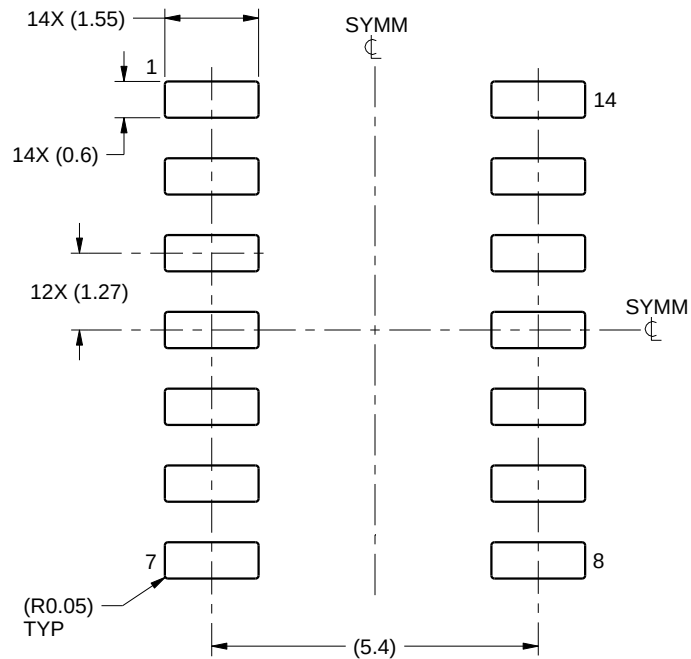
**NOTES:**

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

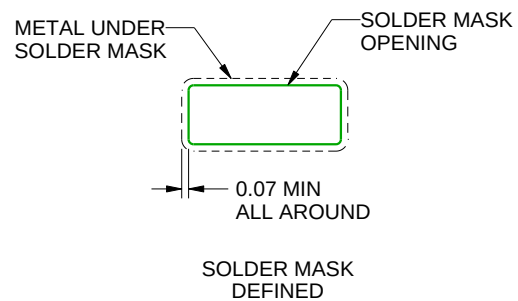
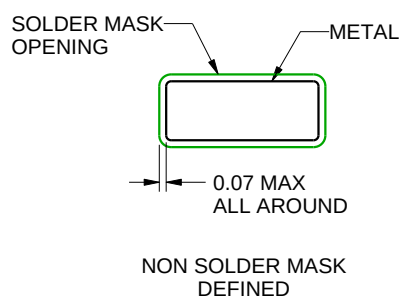
**D0014A**

**SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
SCALE:8X



## SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

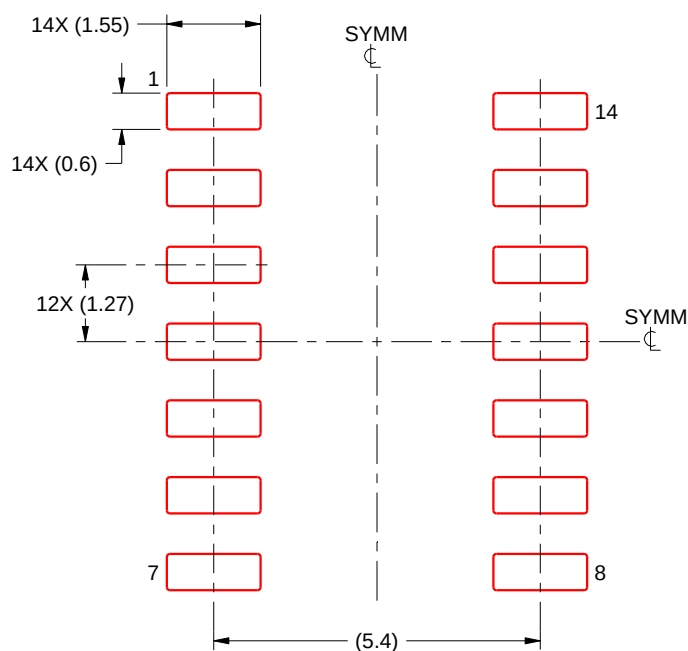


## EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

## GENERIC PACKAGE VIEW

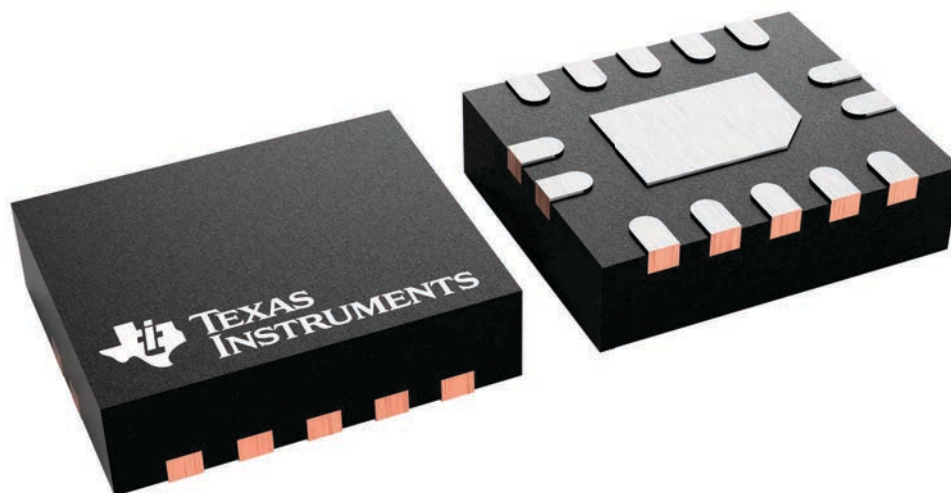
**BQA 14**

**WQFN - 0.8 mm max height**

2.5 x 3, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

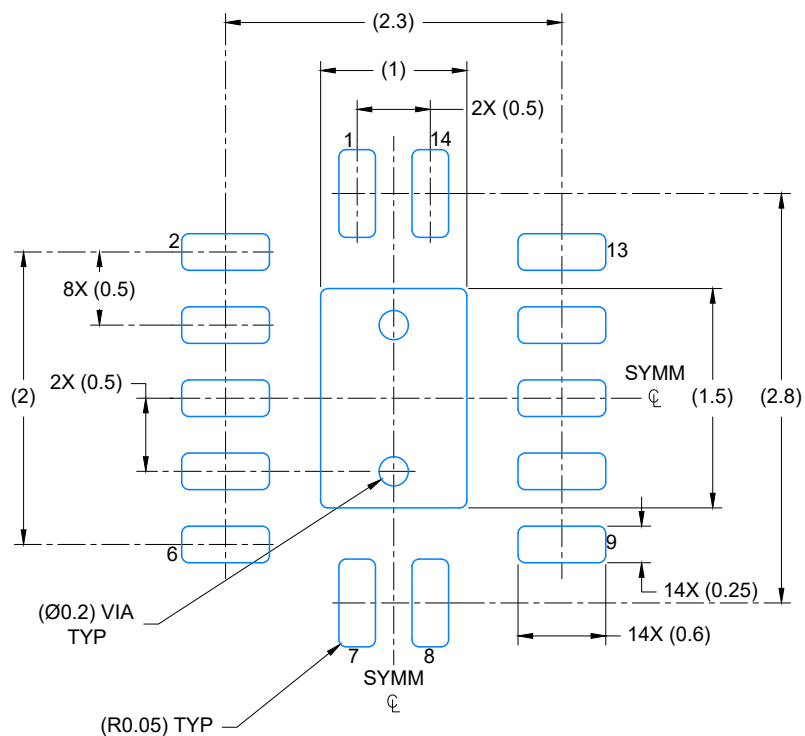
This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



## PLASTIC QUAD FLAT PACK-NO LEAD



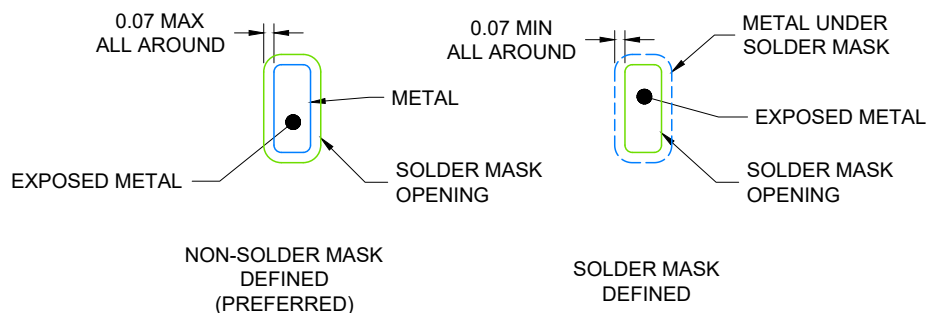
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



## LAND PATTERN EXAMPLE

EXPOSED METAL SHOWN

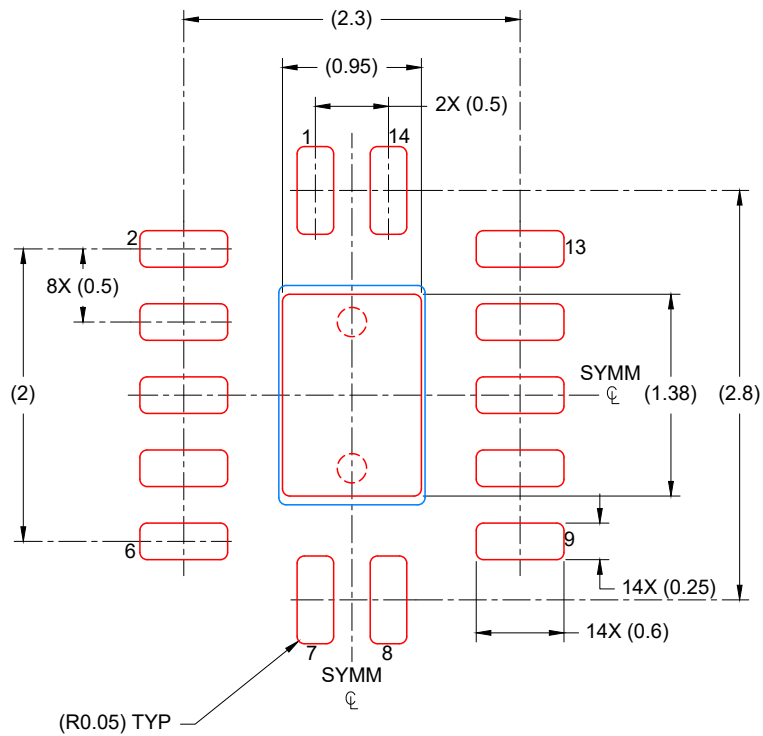
SCALE: 20X



4224636/A 11/2018

## NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slue271](http://www.ti.com/lit/slue271)).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



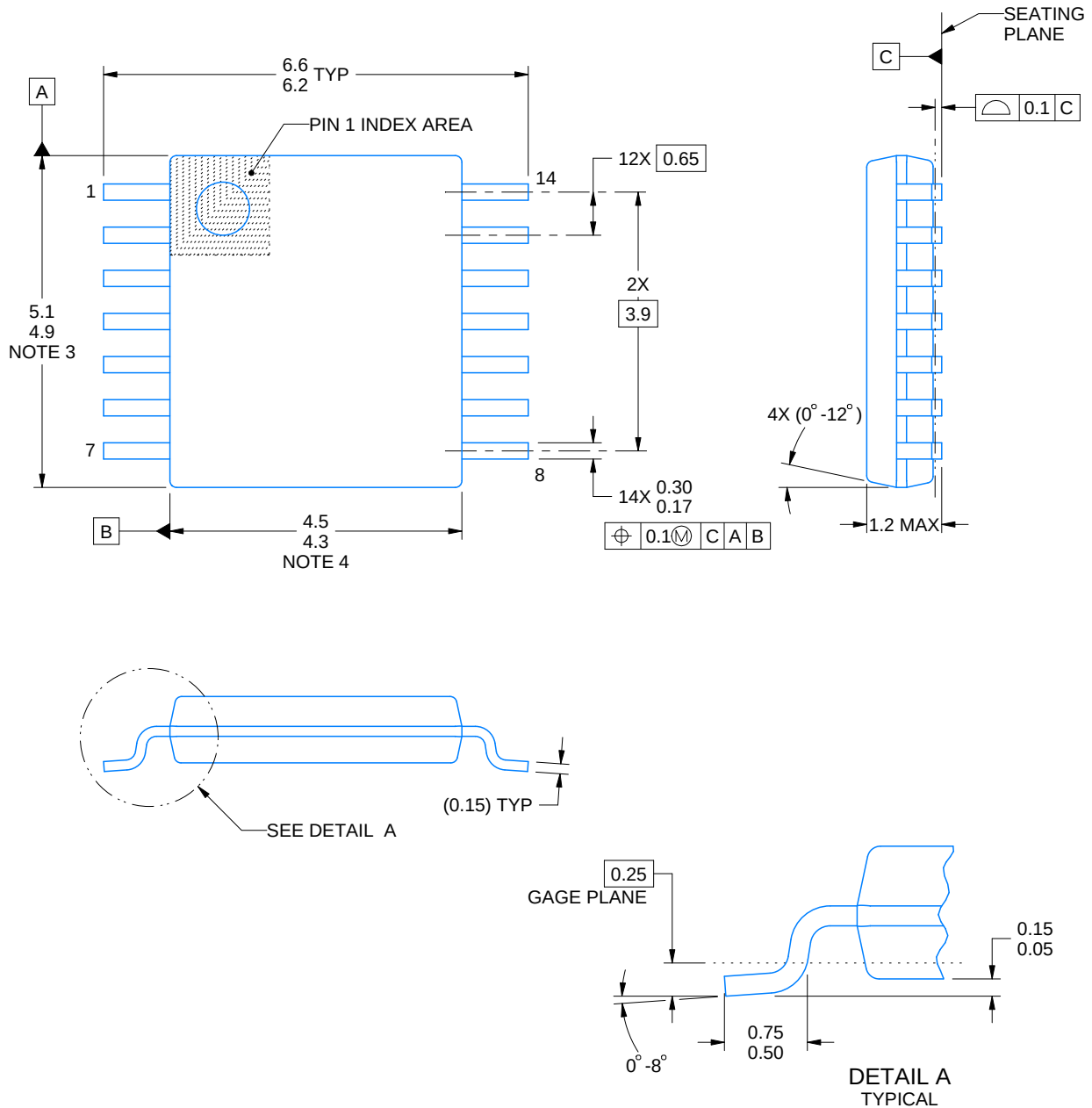
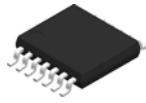
SOLDER PASTE EXAMPLE  
 BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD  
 88% PRINTED COVERAGE BY AREA  
 SCALE: 20X

4224636/A 11/2018

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



4220202/B 12/2023

## NOTES:

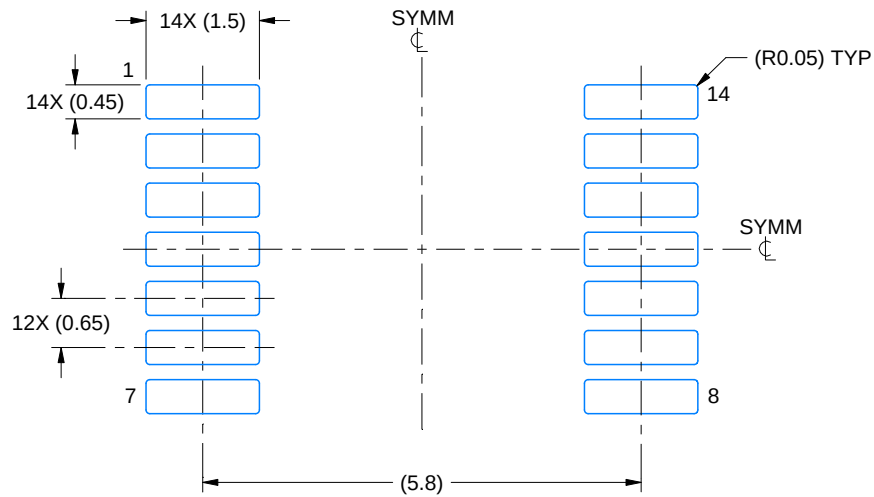
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

# EXAMPLE BOARD LAYOUT

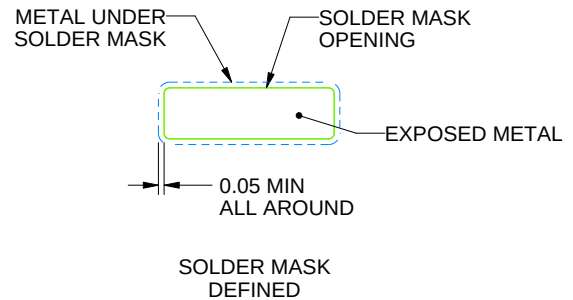
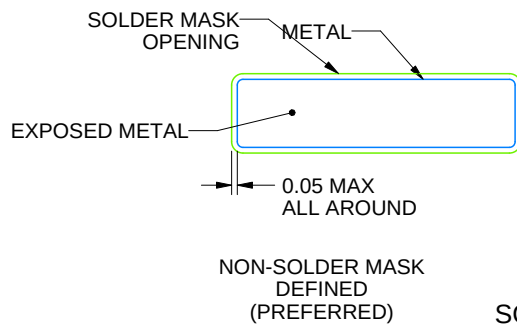
PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 10X



SOLDER MASK DETAILS

4220202/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

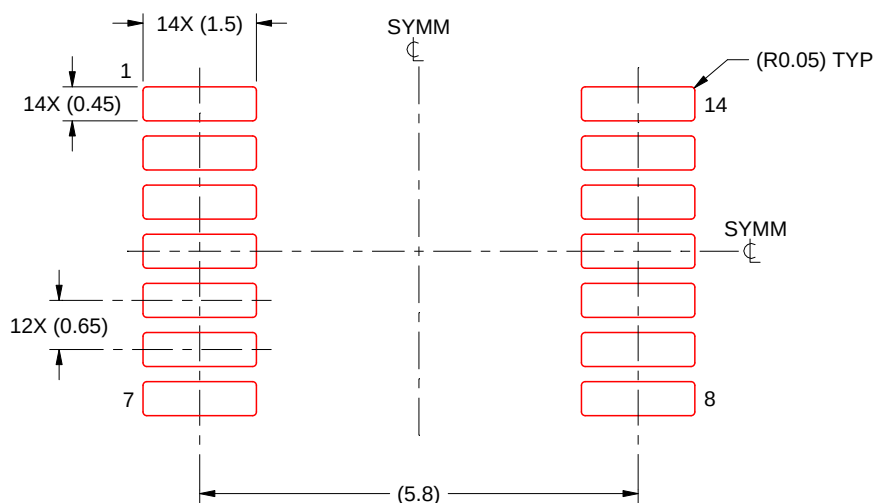
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



## 重要なお知らせと免責事項

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